

ABSTRACT OF THE DISCLOSURE

An electro-optical device includes a TFT, a data line, a scanning line, and a pixel electrode, which are provided above a substrate, a semiconductor layer which constitutes the TFT being connected to the pixel electrode through a relay film. A light-shielding conductive film provided between the data line and the relay film is electrically connected to a capacitor electrode which consists of the same film as the scanning line provided between the relay film and the semiconductor layer at a constant potential, thereby forming a storage capacitor between the films. Therefore, in an electro-optical device of a type in which a light-shielding film against incident light is provided above pixel switching TFT, and a light-shielding film against returned light is provided below the TFT, the pixel aperture ratio can be increased, and the storage capacitor can be enlarged.